

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
100V	280mΩ@10V	2A
	310mΩ@4.5V	

Feature

- Trench power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Suffix "-Q1" for AEC-Q101

Application

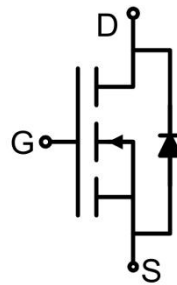
- DC-DC Converters
- Power management functions

Package

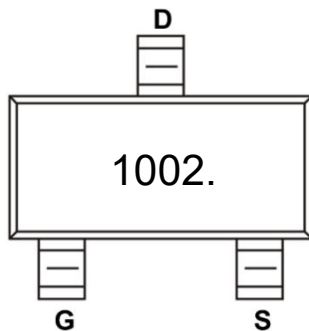


SOT-23

Circuit diagram



Marking



Absolute maximum ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	2	A
Continuous Drain Current ($T_A=70^\circ\text{C}$)	$I_{D(70^\circ\text{C})}$	1.6	A
Pulsed Drain Current ¹⁾	I_{DM}	8	A
Power Dissipation	P_D	1.3	W
Thermal Resistance from Junction to Ambient ²⁾	$R_{\theta JA}$	96	$^\circ\text{C}/\text{W}$
Operating Junction Temperature	T_J	-55 ~ +150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Electrical characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu\text{A}$	100			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.1	1.8	2.5	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 2A$		250	280	m Ω
		$V_{GS} = 4.5V, I_D = 1A$		260	310	
Dynamic characteristics³⁾						
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1\text{MHz}$		387		pF
Output Capacitance	C_{oss}			31		
Reverse Transfer Capacitance	C_{rss}			28		
Gate Charge	Q_g	$V_{DS} = 50V, V_{GS} = 10V, I_D = 2A$		9.56		nC
Gate-Source Charge	Q_{gs}			1.81		
Gate-Drain Charge	Q_{gd}			1.97		
Turn-on delay time	$t_{d(on)}$	$V_{DS} = 50V, V_{GS} = 10V, I_D = 1.3A$ $R_{GEN} = 1\Omega$		4		nS
Turn-on rise time	t_r			17.8		
Turn-off delay time	$t_{d(off)}$			13.2		
Turn-off fall time	t_f			28		
Source-Drain Diode characteristics						
Diode Forward current	I_S				2	A
Diode Forward voltage	V_{SD}	$V_{GS} = 0V, I_S = 2A$			1.2	V
Reverse Recovery Time	T_{rr}	$I_F = 2A, di/dt = -100A/\mu\text{s}$		36.1		nS
Reverse Recovery Charge	Q_{rr}			14.4		nC

Notes:

- 1) Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.
- 2) $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.
- 3) Guaranteed by design, not subject to production testing.

Typical Characteristics

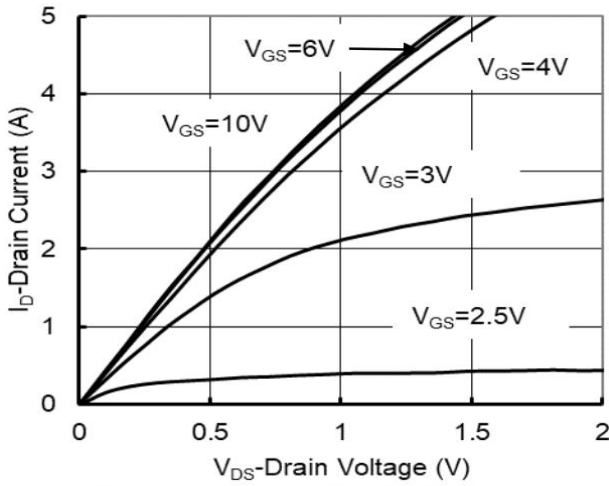


Figure1. Output Characteristics

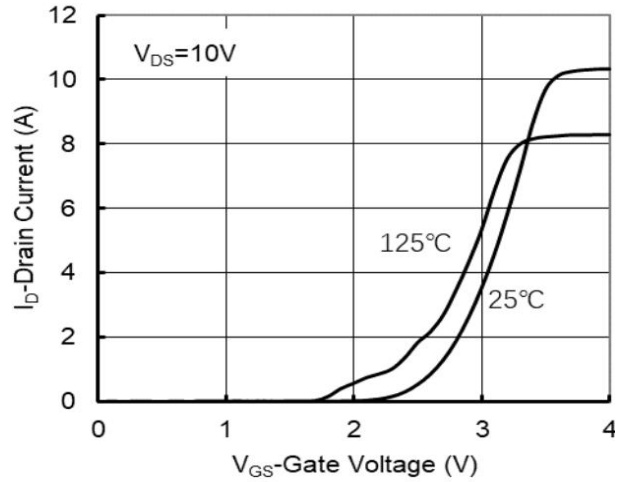


Figure2. Transfer Characteristics

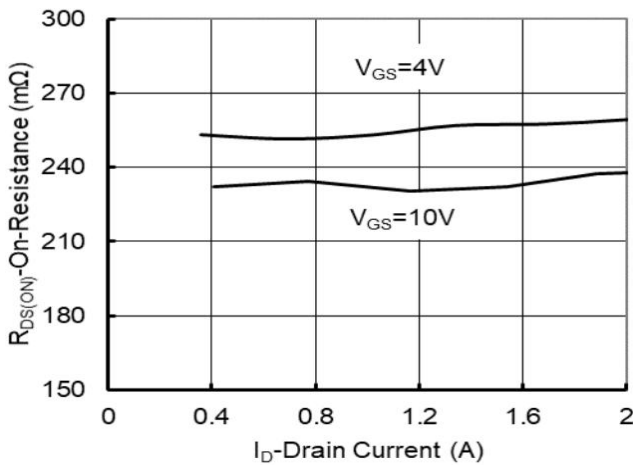


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

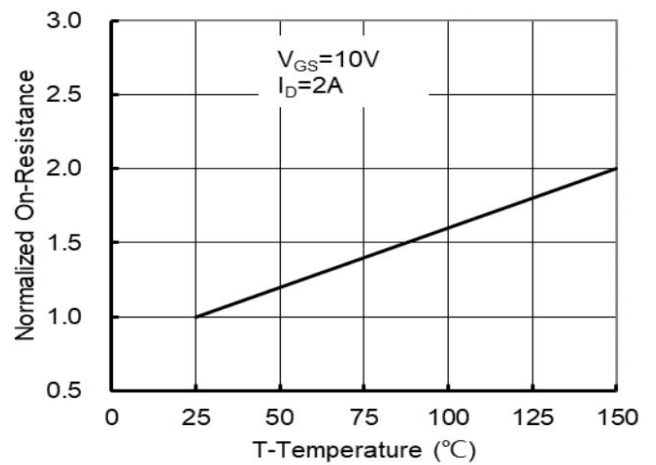


Figure 4: On-Resistance vs. Junction Temperature

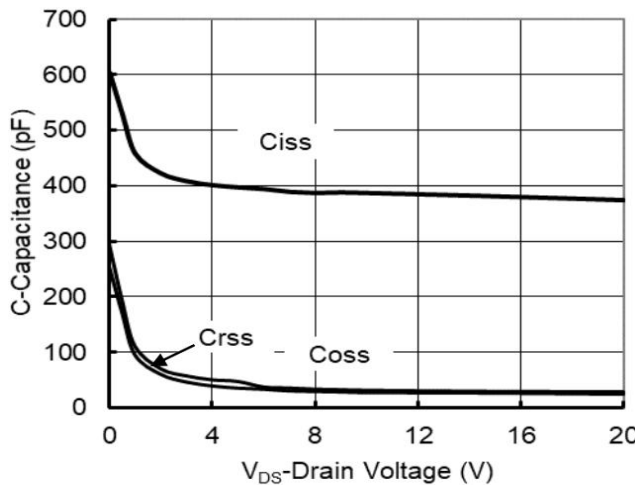


Figure5. Capacitance Characteristics

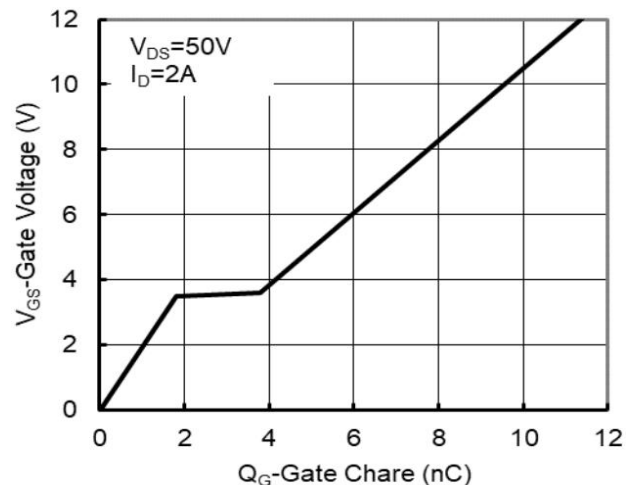


Figure6. Gate Charge

Typical Characteristics

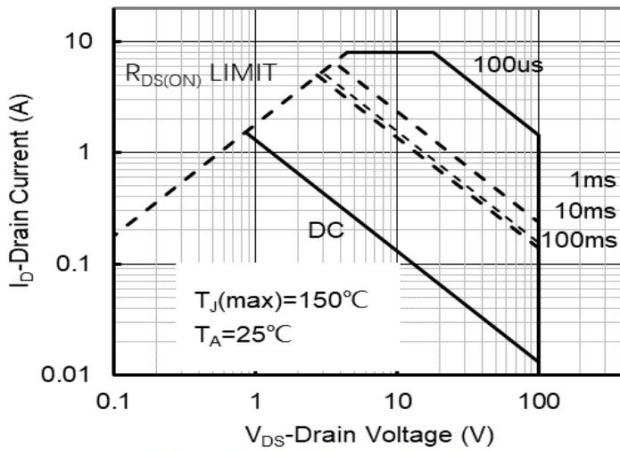


Figure 7. Safe Operation Area

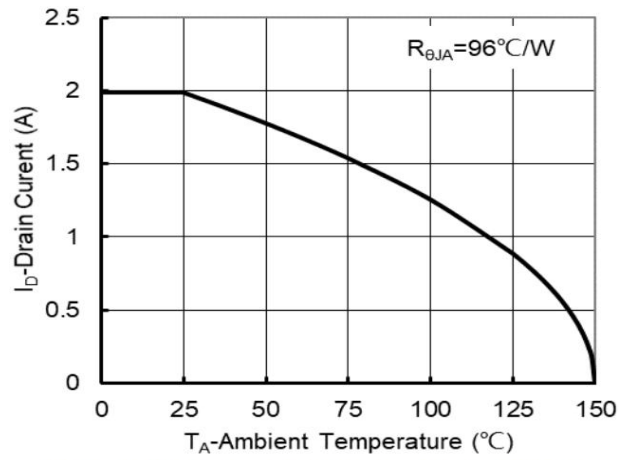


Figure 8. Maximum Continuous Drain Current vs Ambient Temperature

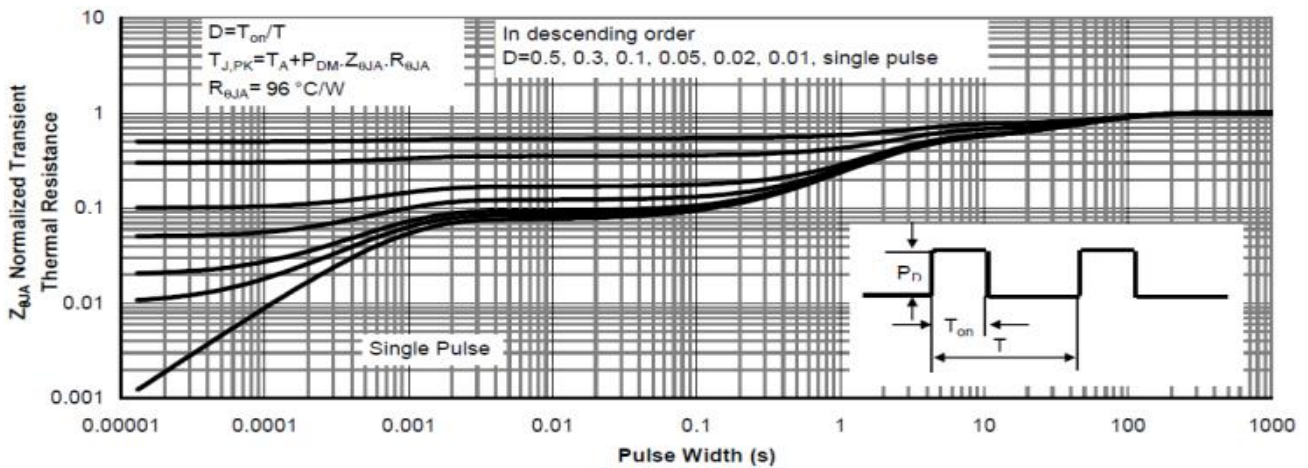
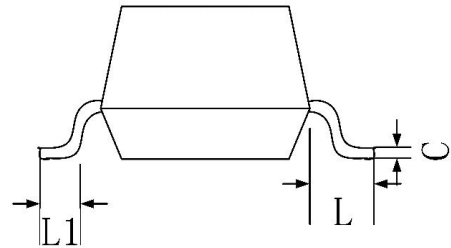
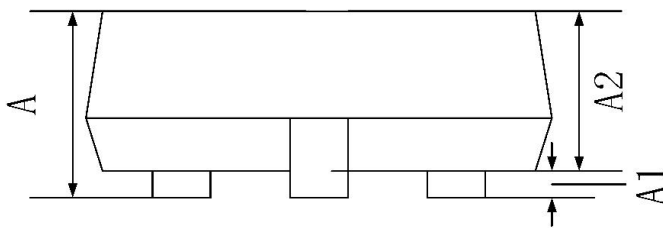
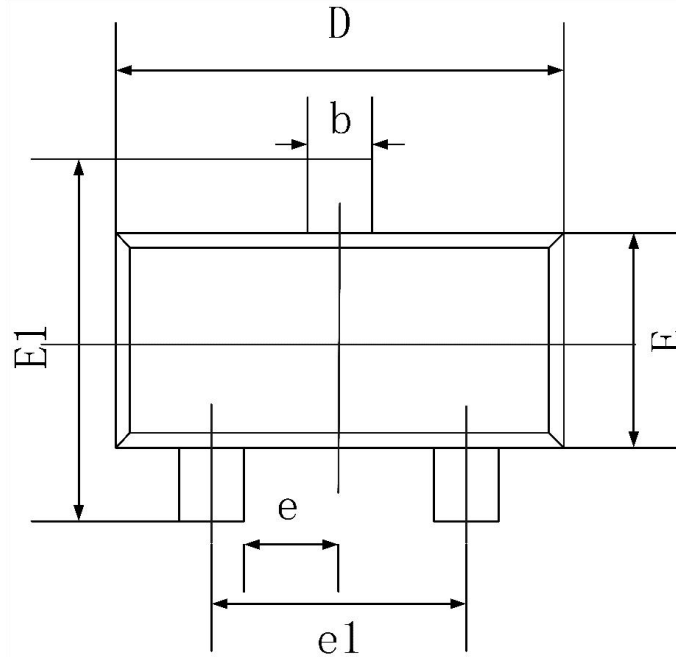


Figure 9. Normalized Maximum Transient Thermal Impedance

SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°